MPSA44U

NPN Silicon Epitaxial Planar Transistor

Features

• Low Collector Emitter Saturation Voltage

1 2 3

1.Base 2.Collector 3.Emitter SOT-89 Plastic Package

Applications

• For high voltage switching and amplifier applications.

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit	
Collector Base Voltage	V _{CBO}	500	V	
Collector Emitter Voltage	V _{CEO}	400	V	
Emitter Base Voltage	V _{EBO}	6	V	
Collector Current	Ic	300	mA	
Total Power Dissipation	P _{tot}	625	mW	
Junction Temperature	Tj	150	°C	
Storage Temperature Range	T _{stg}	- 55 to + 150	°C	

Thermal Characteristics

Parameter	Symbol	Max.	Unit	
Thermal Resistance from Junction to Ambient 1)	Reja	200	°C/W	

¹⁾Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layou



MPSA44U

Characteristics at $T_a = 25$ °C

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at V_{CE} = 10 V, I_C = 1 mA at V_{CE} = 10 V, I_C = 10 mA at V_{CE} = 10 V, I_C = 50 mA at V_{CE} = 10 V, I_C = 100 mA	hfe hfe hfe hfe	40 50 45 40	- 200 - -	- - - -	
Collector Base Cutoff Current at V _{CB} = 400 V	Ісво	-	0.1	μA	
Collector Emitter Cutoff Current at V _{CE} = 400 V	Ices	-	0.5	μA	
Emitter Base Cutoff Current at V _{EB} = 4 V	I _{EBO}	I _{EBO} -		μA	
Collector Base Breakdown Voltage at I _C = 100 μA	V _(BR) CBO	500	-	V	
Collector Emitter Breakdown Voltage at I _C = 1 mA	V _(BR) CEO	400	-	V	
Emitter Base Breakdown Voltage at $I_E = 100 \mu A$	V _{(BR)EBO}	6	-	V	
Collector Emitter Saturation Voltage at I_C = 1 mA, I_B = 0.1 mA at I_C = 10 mA, I_B = 1 mA at I_C = 50 mA, I_B = 5 mA	VCE(sat)	- - -	0.4 0.5 0.75	V V V	
Base Emitter Saturation Voltage at $I_C = 10$ mA, $I_B = 1$ mA	V _{BE(sat)}	-	0.75	V	
Collector Output Capacitance at V _{CB} = 20 V, f = 1 MHz	C _{ob}	-	7	pF	



Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

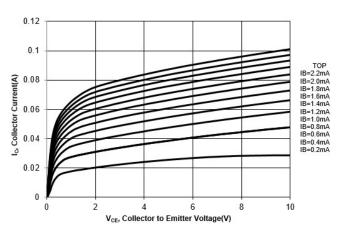


Fig. 2 Collector Current vs. Base to Emitter Voltage

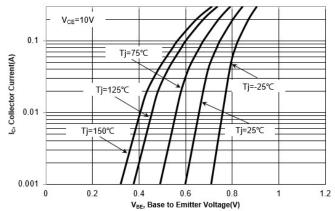


Fig. 3 DC Current Gain vs. Collector Current

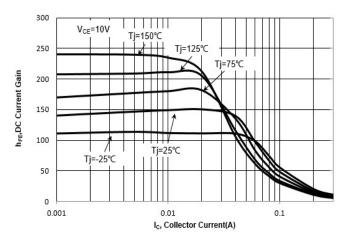
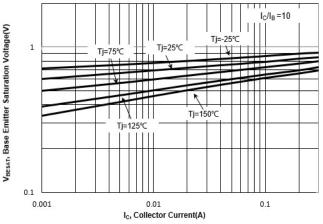


Fig. 4 V_{BESAT} vs. Collector Current





Electrical Characteristics Curves

Fig. 5 V_{CESAT} vs. Collector Current

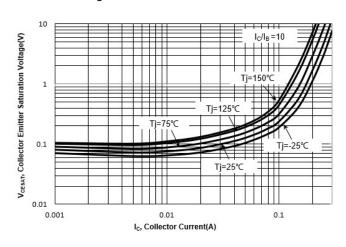


Fig. 6 Output Capacitance

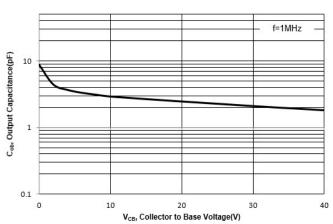
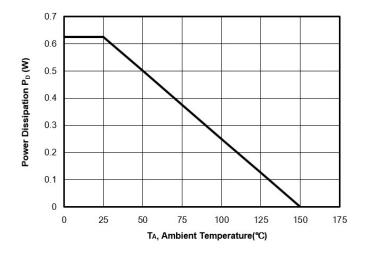


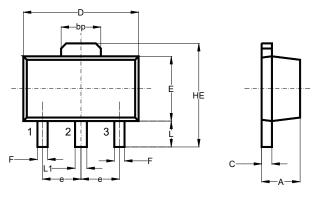
Fig. 7 Power Derating Curve

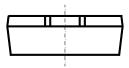




Package Outline (Dimensions in mm)

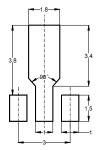
SOT-89





Unit	Α	bp	С	D	Е	F	HE	е	L	L1
	1.6	1.60	0.5	4.6	2.6	0.45	4.25	1.5	1.05	0.51
mm	1.4	1.50	0.3	4.4	2.4	0.35	3.75	typ.	0.95	0.41

Recommended Soldering Footprint



Packing information

i dokang anomadon						
	Tape Width (mm)	Pitch		Reel Size		
Package		mm	inch	mm	inch	Per Reel Packing Quantity
207.00	40	0 . 0 4	0.045 + 0.004	178	7	1,000
SOT-89	12	8 ± 0.1	0.315 ± 0.004	330	13	4,000

Marking information

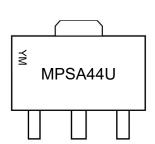
" MPSA44U " = Part No.

"YM" = Date Code Marking

"Y" = Year

"M" = Month

Font type: Arial



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